



# PDTC143TMB

NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = open

Rev. 2 — 4 May 2012

Product data sheet

## 1. Product profile

### 1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA143TMB.

### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

### 1.3 Applications

- Low-current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

### 1.4 Quick reference data

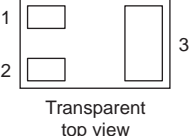
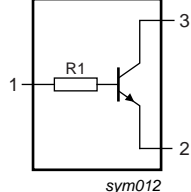
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current		-	-	100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	3.3	4.7	6.1	k $\Omega$



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	 <p>Transparent top view</p> <p><b>SOT883B (DFN1006B-3)</b></p>	 <p><i>sym012</i></p>
2	G	GND (emitter)		
3	O	output (collector)		

## 3. Ordering information

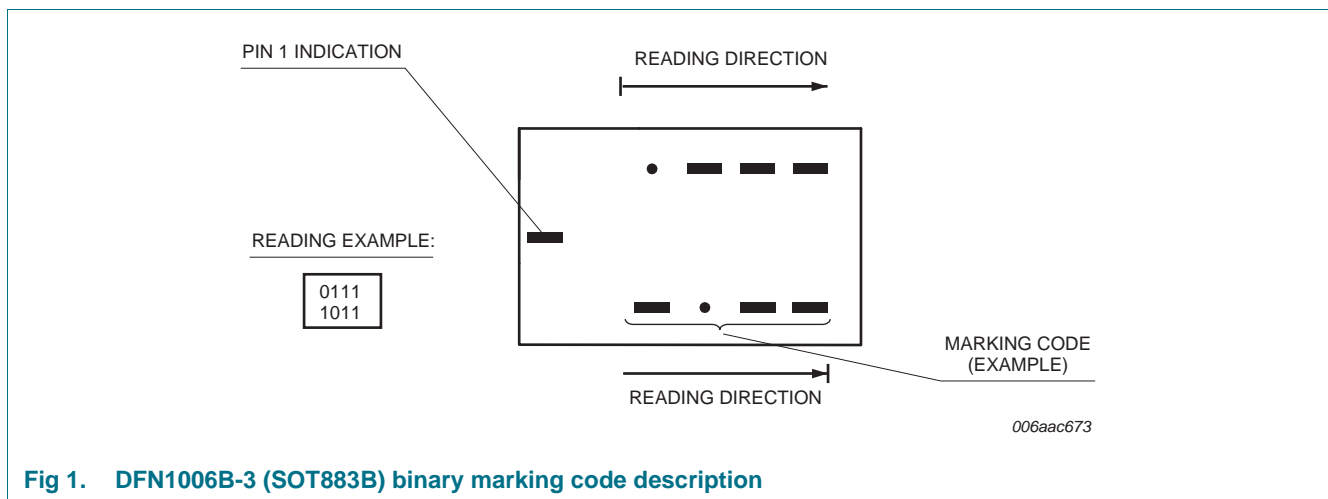
**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PDTC143TMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

## 4. Marking

**Table 4. Marking codes**

Type number	Marking code
PDTC143TMB	0011 1011



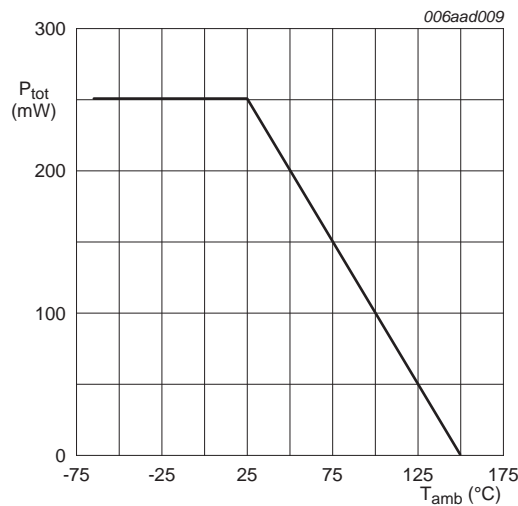
## 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>O</sub>	output current		-	100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	250	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

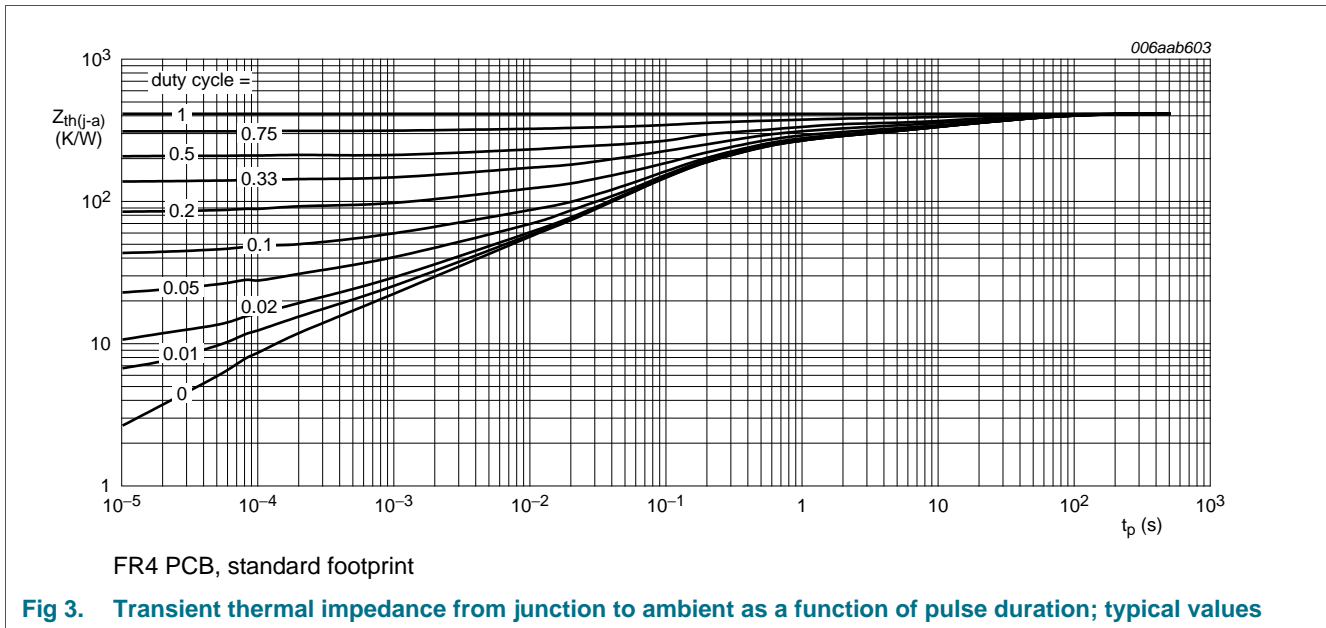
**Fig 2. Power derating curve for DFN1006B-3 (SOT883B)**

## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air <a href="#">[1]</a>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

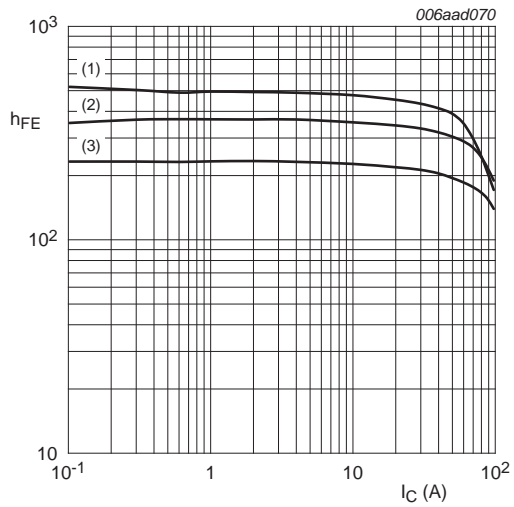


## 7. Characteristics

**Table 7. Characteristics**

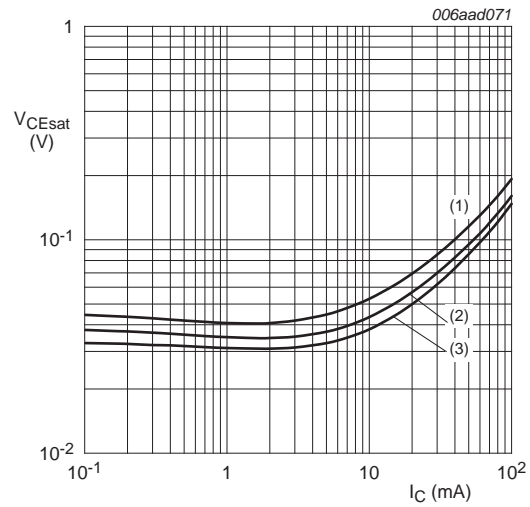
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ °C}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_{amb} = 25\text{ °C}$	-	-	1	μA
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ °C}$	-	-	5	μA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ °C}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}; T_{amb} = 25\text{ °C}$	200	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 5\text{ mA}; I_B = 0.25\text{ mA}; T_{amb} = 25\text{ °C}$	-	-	100	mV
R1	bias resistor 1 (input)	$T_{amb} = 25\text{ °C}$	3.3	4.7	6.1	kΩ
$C_C$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A}; f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$	-	-	2.5	pF
$f_T$	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}; T_{amb} = 25\text{ °C}$ <a href="#">[1]</a>	-	230	-	MHz

[1] Characteristics of built-in transistor.



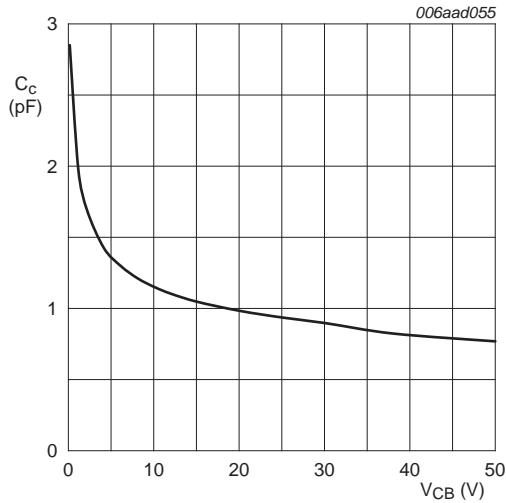
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -40\text{ °C}$

**Fig 4. DC current gain as a function of collector current; typical values**



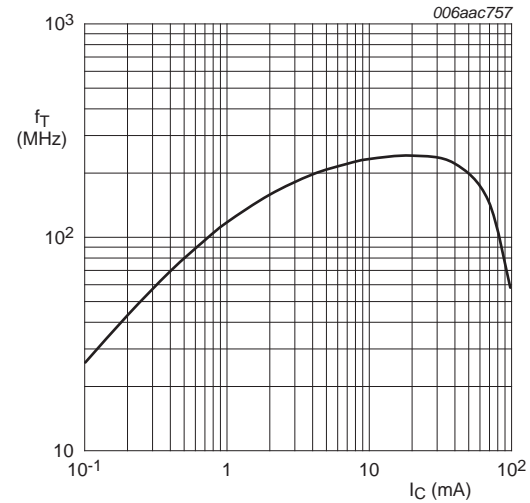
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -40\text{ °C}$

**Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values**



$f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$

**Fig 6. Collector capacitance as a function of collector-base voltage; typical values of built-in transistor**



$V_{CE} = 5\text{ V}; T_{amb} = 25\text{ °C}$

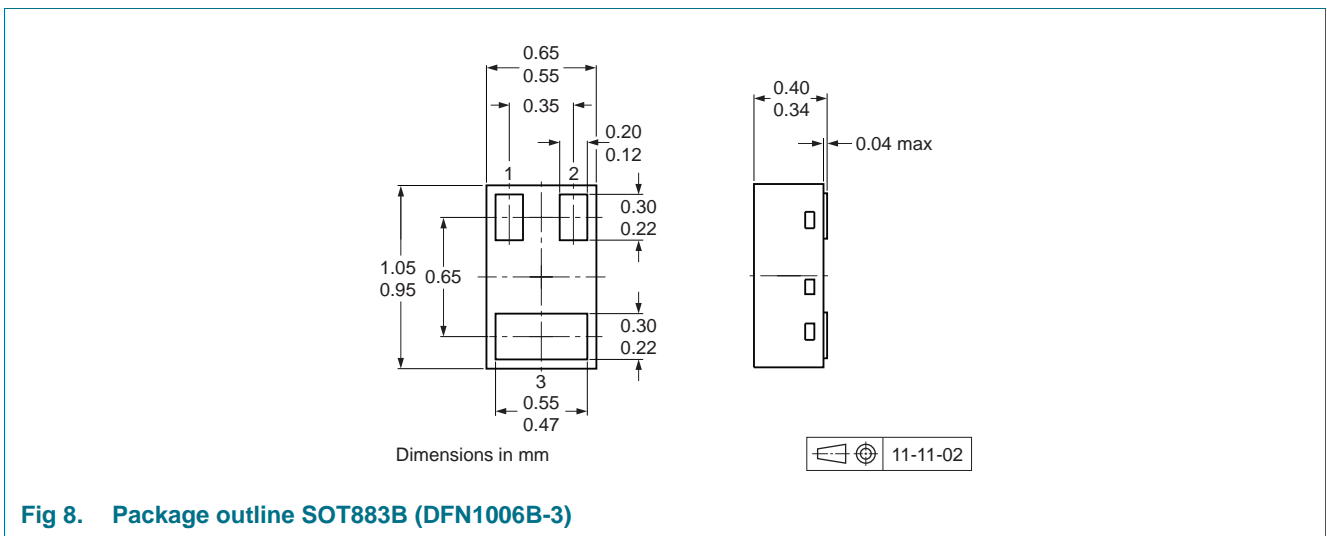
**Fig 7. Transition frequency as a function of collector current; typical values of built-in transistor**

## 8. Test information

### 8.1 Quality information

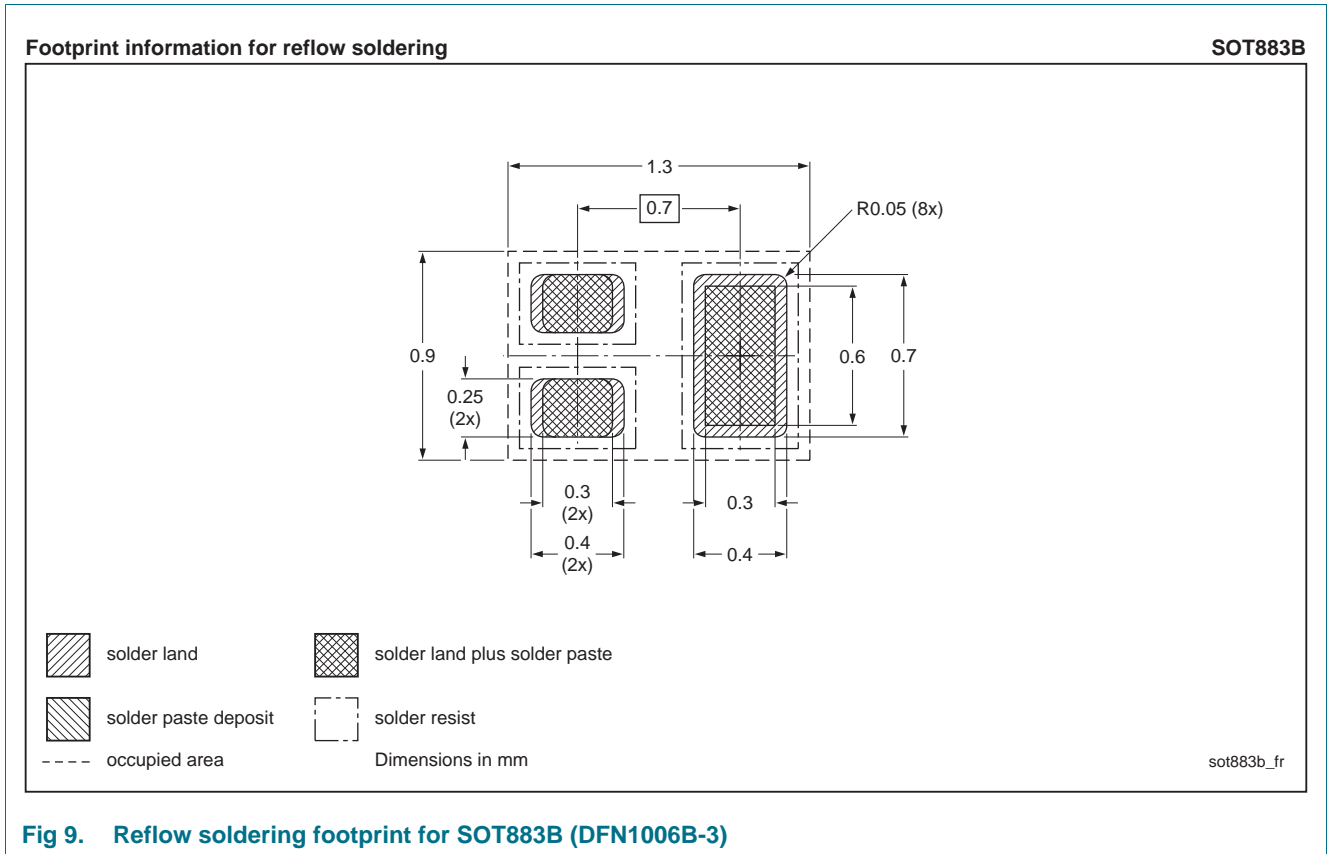
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline



**Fig 8. Package outline SOT883B (DFN1006B-3)**

## 10. Soldering



**Fig 9. Reflow soldering footprint for SOT883B (DFN1006B-3)**

## 11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC143TMB v.2	20120504	Product data sheet	-	PDTC143TMB v.1
Modifications:	• <a href="#">7 "Characteristics"</a> : parameter name corrected			
PDTC143TMB v.1	20120425	Product data sheet	-	-



## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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